

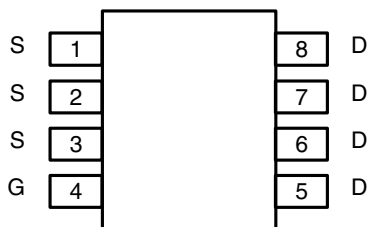


# N-Channel 30 V (D-S) MOSFET with Schottky Diode

## PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ ) Max.	$I_D$ (A) <sup>a</sup>	$Q_g$ (Typ.)
30	0.016 at $V_{GS} = 10$ V	11.9	5.5 nC
	0.020 at $V_{GS} = 4.5$ V	10.6	

SO-8



Top View

### Ordering Information:

Si4776DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

## FEATURES

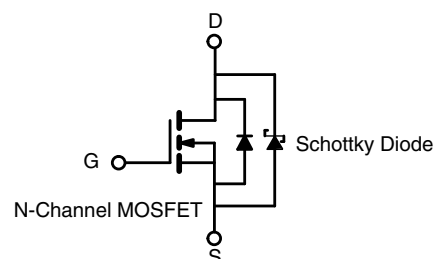
- Halogen-free According to IEC 61249-2-21 Definition
- SkyFET<sup>®</sup> Monolithic TrenchFET<sup>®</sup> Power MOSFET and Schottky Diode
- 100 %  $R_g$  and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## APPLICATIONS

- Notebook System Power and Memory - Low Side



## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	A
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Pulsed Drain Current ( $t = 300$ $\mu$ s)	$I_{DM}$	50	A
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25$ °C	
		$T_A = 25$ °C	
Single Pulse Avalanche Current	$I_{AS}$	10	mJ
Single Pulse Avalanche Energy	$E_{AS}$	5	
Maximum Power Dissipation	$P_D$	$T_C = 25$ °C	W
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	$R_{thJA}$	40	50	°C/W
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	24	30	

Notes:

a. Based on  $T_C = 25$  °C.

b. Surface mounted on 1" x 1" FR4 board.

c.  $t = 10$  s.

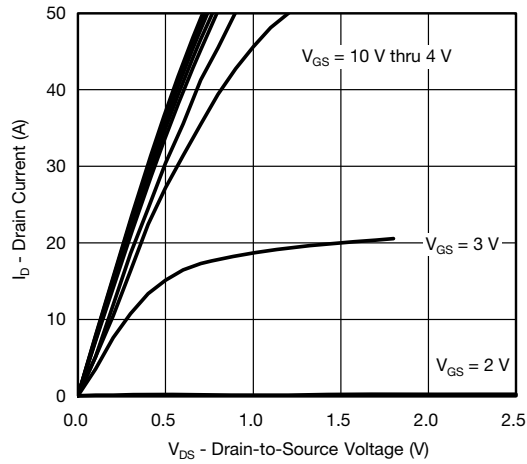
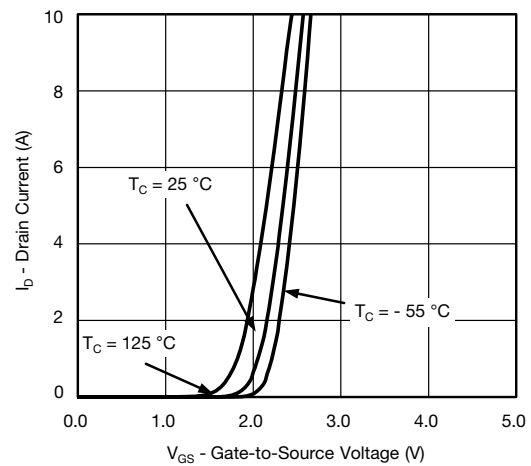
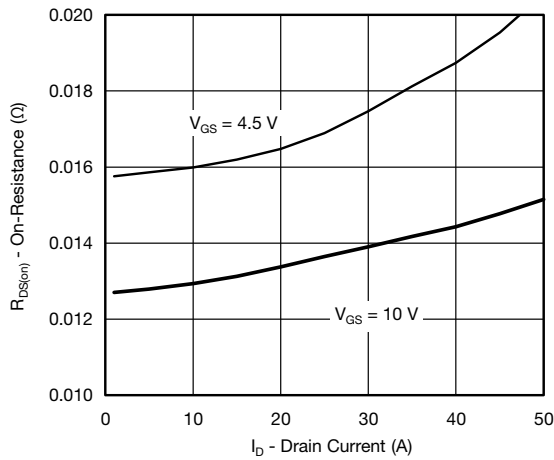
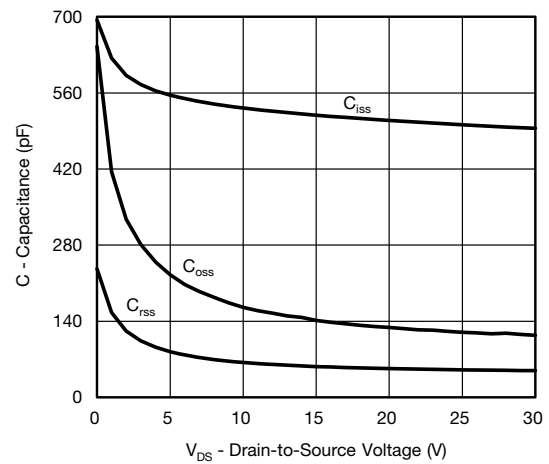
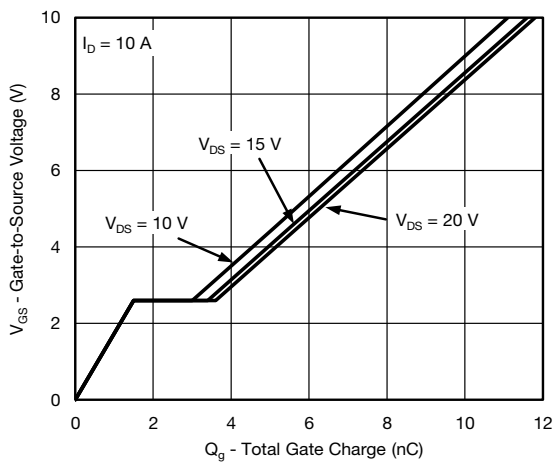
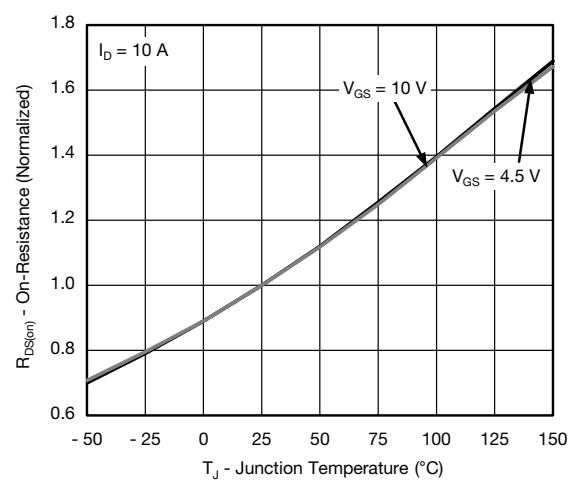
d. Maximum under steady state conditions is 95 °C/W.

SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = 1 mA	30			V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1 mA	1		2.3	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V		0.013	0.150	mA
		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 100 °C		1	10	
On -State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	30			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		0.013	0.016	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 7 A		0.016	0.020	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		30		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz		521		pF
Output Capacitance	C <sub>oss</sub>			141		
Reverse Transfer Capacitance	C <sub>rss</sub>			57		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		11.6	17.5	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A		5.5	8.5	
Gate-Drain Charge	Q <sub>gd</sub>			1.5		
Gate Resistance	R <sub>g</sub>			1.9		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.2	0.8	1.6	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 1.5 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω		12	24	ns
Rise Time	t <sub>r</sub>			12	24	
Turn-Off Delay Time	t <sub>d(off)</sub>			14	28	
Fall Time	t <sub>f</sub>			8	16	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 1.5 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω		10	20	
Rise Time	t <sub>r</sub>			11	22	
Turn-Off Delay Time	t <sub>d(off)</sub>			11	22	
Fall Time	t <sub>f</sub>			6	12	
Drain-Source Body Diode and Schottky Characteristics						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			3.7	A
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				50	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1 A		0.44	0.55	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 5 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C		12	24	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			4.5	9	nC
Reverse Recovery Fall Time	t <sub>a</sub>			6.5		ns
Reverse Recovery Rise Time	t <sub>b</sub>			5.5		

## Notes:

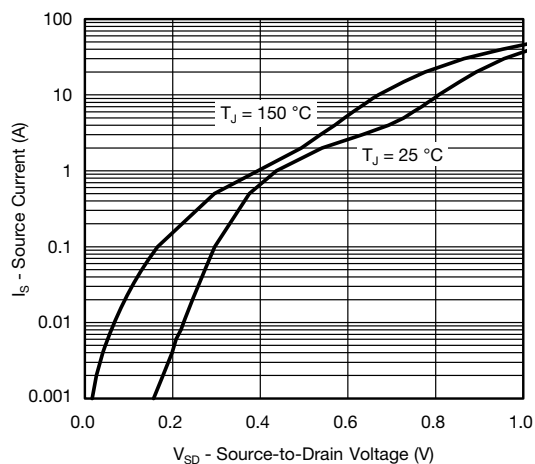
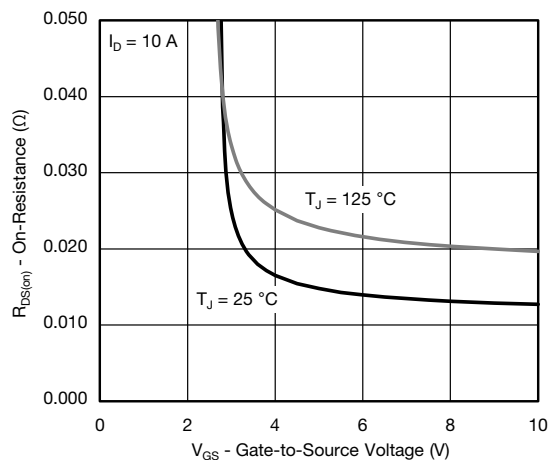
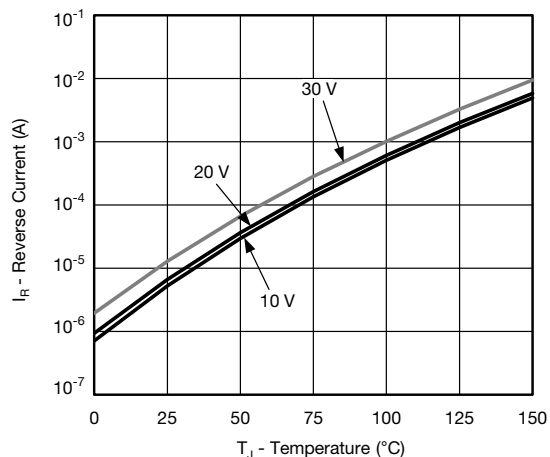
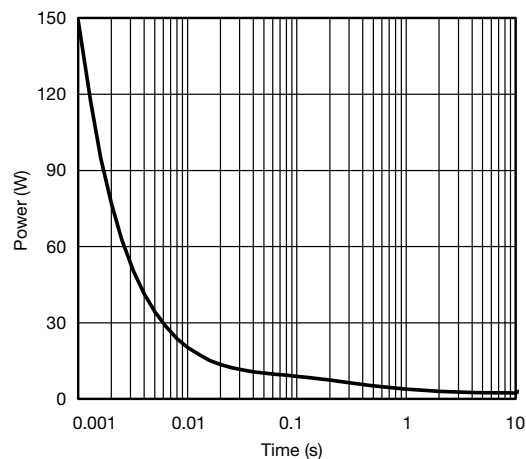
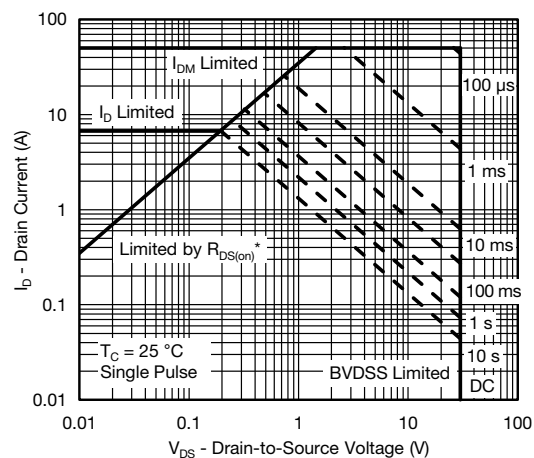
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

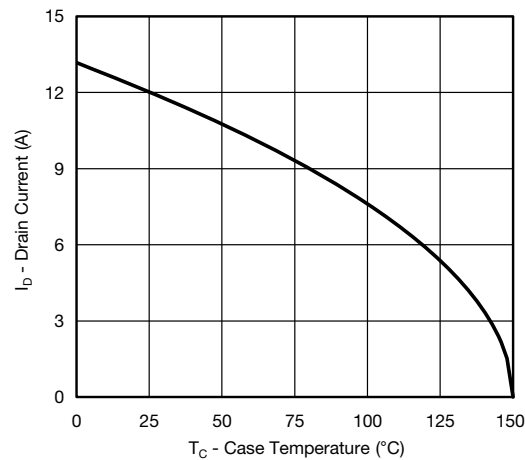
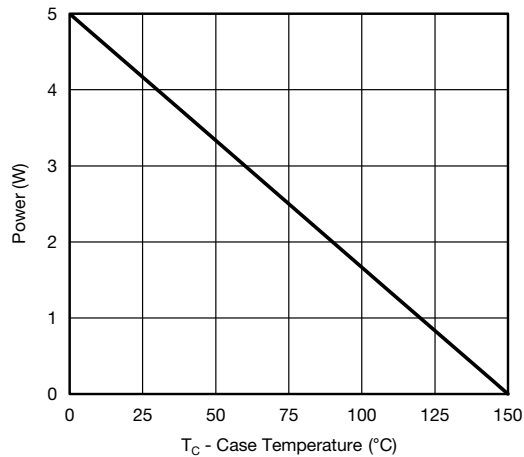
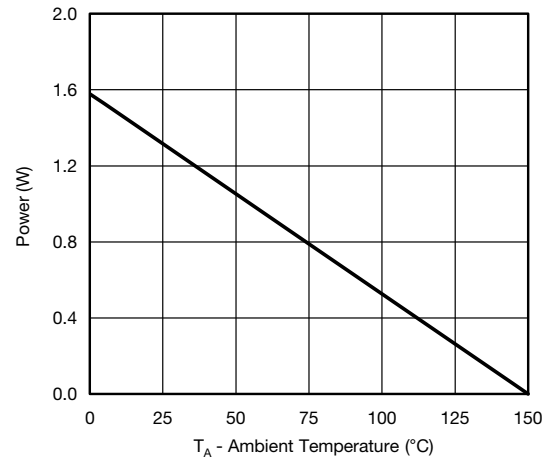
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.


**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**

**Si4776DY**

Vishay Siliconix

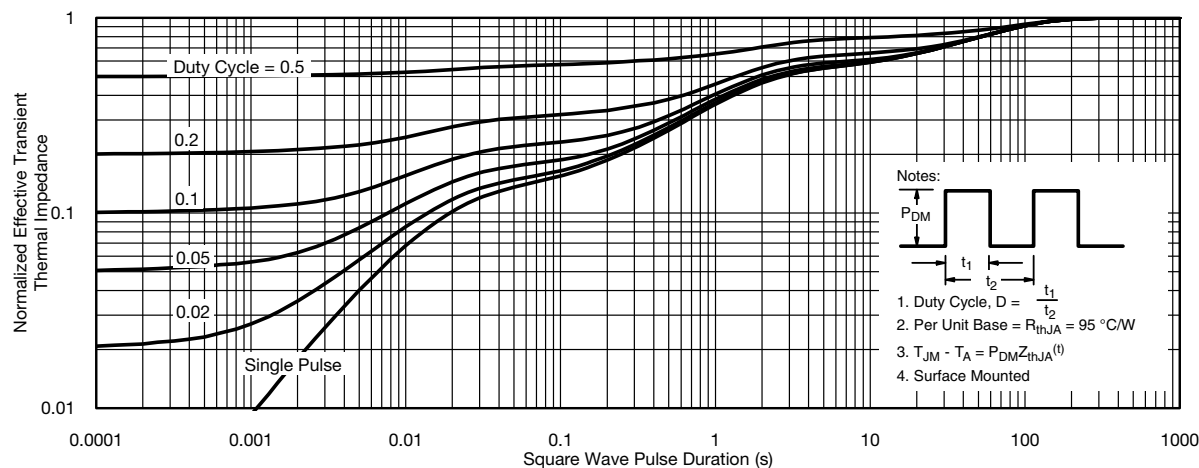
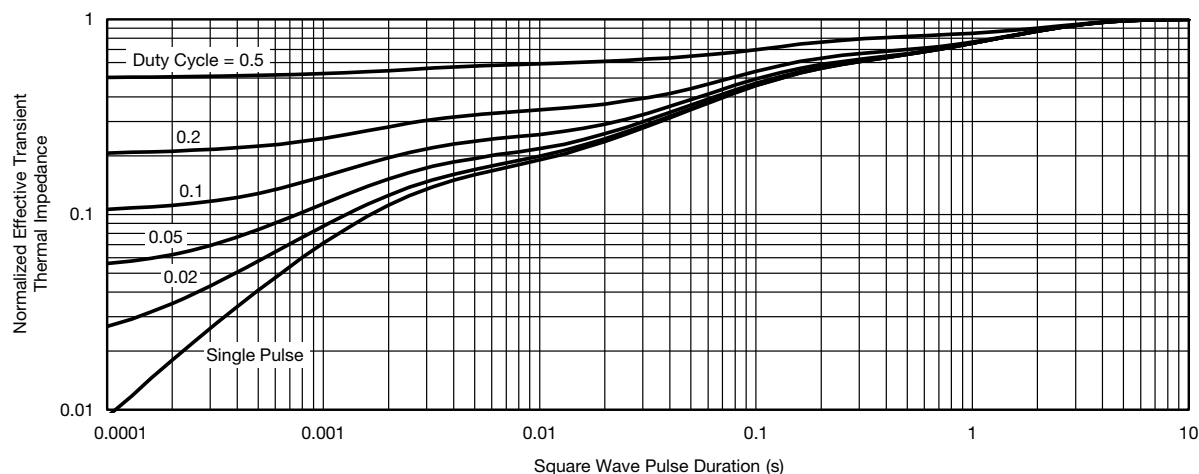
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Reverse Current (Schottky)****Single Pulse Power, Junction-to-Ambient**\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified**Safe Operating Area**


**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Current Derating\***

**Power Derating, Junction-to-Foot**

**Power Derating, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**Si4776DY**

Vishay Siliconix

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?63316](http://www.vishay.com/ppg?63316).

## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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